

Shan Guan

List of Publications by Year in descending order

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13
papers

1,294
citations

687363

13
h-index

1125743

13
g-index

13
all docs

13
docs citations

13
times ranked

1735
citing authors

#	ARTICLE	IF	CITATIONS
1	Bi_2Te_3 -GeSe: A two-dimensional ferroelectric material with doping-induced ferromagnetism. Applied Physics Letters, 2019, 115, .	3.3	41
2	Tunable ferroelectricity and anisotropic electric transport in monolayer Bi_2Te_3 -GeSe. Physical Review B, 2018, 97, .	3.2	72
3	Nonsymmorphic-symmetry-protected hourglass Dirac loop, nodal line, and Dirac point in bulk and monolayer Bi_2Te_3 (Bi_2Te_3 = Bi_2Te_3) Tj ETQq1 1 0.784314 rgBT	3.2	116
4	Artificial gravity field, astrophysical analogues, and topological phase transitions in strained topological semimetals. Npj Quantum Materials, 2017, 2, .	5.2	116
5	Computational characterization of monolayer C ₃ N: A two-dimensional nitrogen-graphene crystal. Journal of Materials Research, 2017, 32, 2993-3001.	2.6	110
6	Tunable half-metallic magnetism in an atom-thin holey two-dimensional C ₂ N monolayer. Journal of Materials Chemistry C, 2017, 5, 8424-8430.	5.5	39
7	Type-II nodal loops: Theory and material realization. Physical Review B, 2017, 96, .	3.2	158
8	Tunable hyperbolic dispersion and negative refraction in natural electride materials. Physical Review B, 2017, 95, .	3.2	56
9	Two-dimensional spin-orbit Dirac point in monolayer HfGeTe. Physical Review Materials, 2017, 1, .	2.4	70
10	Electronic, Dielectric and Plasmonic Properties of Two-Dimensional Electride Materials X ₂ N (X=Ca,) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50	3.3	73
11	Effects of strain on electronic and optic properties of holey two-dimensional C ₂ N crystals. Applied Physics Letters, 2015, 107, .	3.3	144
12	2D Electrides as Promising Anode Materials for Na-Ion Batteries from First-Principles Study. ACS Applied Materials & Interfaces, 2015, 7, 24016-24022.	8.0	181
13	Low-energy effective hamiltonian for giant-gap quantum spin Hall insulators in honeycomb Bi_2Te_3 (Bi_2Te_3 = Bi_2Te_3) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50	3.2	119
	2014, 90, .		